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# **Analog Multiplexers** / **Demultiplexers**

# **High-Performance Silicon-Gate CMOS**

The MC74HC4051A, MC74HC4052A and MC74HC4053A utilize silicon-gate CMOS technology to achieve fast propagation delays, low ON resistances, and low OFF leakage currents. These analog multiplexers/demultiplexers control analog voltages that may vary across the complete power supply range (from V<sub>CC</sub> to V<sub>EE</sub>).

The HC4051A, HC4052A and HC4053A are identical in pinout to the metal-gate MC14051AB, MC14052AB and MC14053AB. The Channel-Select inputs determine which one of the Analog Inputs/Outputs is to be connected, by means of an analog switch, to the Common Output/Input. When the Enable pin is HIGH, all analog switches are turned off.

The Channel–Select and Enable inputs are compatible with standard CMOS outputs; with pullup resistors they are compatible with LSTTL outputs.

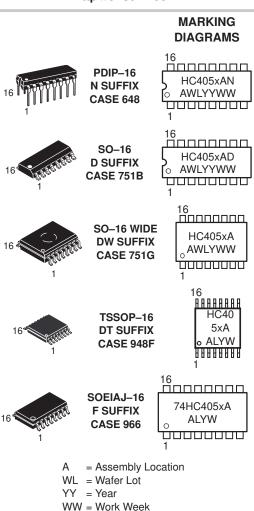
These devices have been designed so that the ON resistance  $(R_{OD})$  is more linear over input voltage than Ron of metal-gate CMOS analog

For a multiplexer/demultiplexer with injection current protection, see HC4851A and HC4852A.

- Fast Switching and Propagation Speeds
- Low Crosstalk Between Switches
- Diode Protection on All Inputs/Outputs
- Analog Power Supply Range  $(V_{CC} V_{EE}) = 2.0$  to 12.0 V
- Digital (Control) Power Supply Range  $(V_{CC} GND) = 2.0$  to 6.0 V
- Improved Linearity and Lower ON Resistance Than Metal-Gate Counterparts
- Low Noise
- In Compliance With the Requirements of JEDEC Standard No. 7A
- HC4051A 184 FETs or 46 Equivalent Gates • Chip Complexity: HC4052A — 168 FETs or 42 Equivalent Gates HC4053A — 156 FETs or 39 Equivalent Gates



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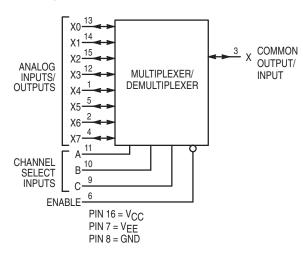


#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 13 of this data sheet.

MC74HC4051A/D

# LOGIC DIAGRAM MC74HC4051A Single-Pole, 8-Position Plus Common Off

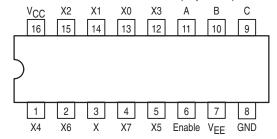


#### **FUNCTION TABLE - MC74HC4051A**

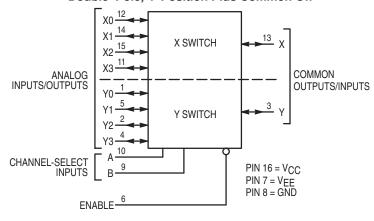
	Contr	ol In			
		Select			
Enab	ole	С	В	Α	ON Channels
L		L	L	L	X0
L		L	L	Н	X1
L		L	Н	L	X2
L		L	Н	Н	X3
L		Н	L	L	X4
L		Н	L	Н	X5
L		Н	Н	L	X6
L		Н	Н	Н	X7
H		Χ	Χ	Χ	NONE

X = Don't Care

### Pinout: MC74HC4051A (Top View)



# LOGIC DIAGRAM MC74HC4052A Double-Pole, 4-Position Plus Common Off

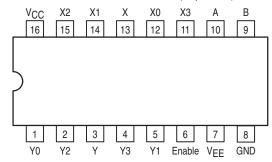


#### **FUNCTION TABLE - MC74HC4052A**

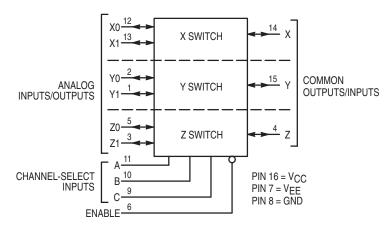
Contr	ol Input	s			
Enable	Sel B	ect A	ON Ch	annels	
L L L	L H H X	L H L H	Y0 Y1 Y2 Y3 NO	X0 X1 X2 X3	

X = Don't Care

## Pinout: MC74HC4052A (Top View)



# LOGIC DIAGRAM MC74HC4053A Triple Single-Pole, Double-Position Plus Common Off



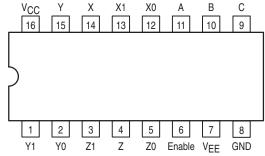
NOTE: This device allows independent control of each switch. Channel–Select Input A controls the X–Switch, Input B controls the Y–Switch and Input C controls the Z–Switch

#### **FUNCTION TABLE - MC74HC4053A**

Con	Control Inputs					
Enable	C	Selec B	t A	10	N Chann	els
L	L	L	L	Z0	Y0	X0
L	L	L	Н	Z0	Y0	X1
L	L	Н	L	Z0	Y1	X0
L	L	Н	Н	Z0	Y1	X1
L	H	L	L	Z1	Y0	X0
L	H	L	Н	Z1	Y0	X1
L	H	Н	L	Z1	Y1	X0
L	H	Н	Н	Z1	Y1	X1
Н	X	Χ	Χ		NONE	

X = Don't Care

## Pinout: MC74HC4053A (Top View)



#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
VCC	Positive DC Supply Voltage (Referenced to GND) (Referenced to VEE)	- 0.5 to + 7.0 - 0.5 to + 14.0	V
VEE	Negative DC Supply Voltage (Referenced to GND)	- 7.0 to + 5.0	V
VIS	Analog Input Voltage	V <sub>EE</sub> – 0.5 to V <sub>CC</sub> + 0.5	V
V <sub>in</sub>	Digital Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I	DC Current, Into or Out of Any Pin	± 25	mA
PD	Power Dissipation in Still Air, Plastic DIP† EIAJ/SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$  VCC. Unused inputs must always be

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

EIAJ/SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

<sup>\*</sup>Maximum Ratings are those values beyond which damage to the device may occur. Functional operation should be restricted to the Recommended Operating Conditions.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
VCC	11,	Referenced to GND) Referenced to V <sub>EE</sub> )	2.0 2.0	6.0 12.0	٧
VEE	Negative DC Supply Voltage, Outpu GND)	ative DC Supply Voltage, Output (Referenced to D)		GND	٧
VIS	Analog Input Voltage		VEE	VCC	V
V <sub>in</sub>	Digital Input Voltage (Referenced to	GND)	GND	VCC	V
V <sub>IO</sub> *	Static or Dynamic Voltage Across St	witch		1.2	V
TA	Operating Temperature Range, All F	Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise/Fall Time (Channel Select or Enable Inputs)	V <sub>CC</sub> = 2.0 V V <sub>CC</sub> = 3.0 V V <sub>CC</sub> = 4.5 V V <sub>CC</sub> = 6.0 V	0 0 0	1000 600 500 400	ns

<sup>\*</sup>For voltage drops across switch greater than 1.2V (switch on), excessive  $V_{CC}$  current may be drawn; i.e., the current out of the switch may contain both  $V_{CC}$  and switch input components. The reliability of the device will be unaffected unless the Maximum Ratings are exceeded.

# DC CHARACTERISTICS — Digital Section (Voltages Referenced to GND) VEE = GND, Except Where Noted

			VCC	Guara	nteed Lim	nit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec	2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
VIL	Maximum Low-Level Input Voltage, Channel-Select or Enable Inputs	R <sub>on</sub> = Per Spec	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
l <sub>in</sub>	Maximum Input Leakage Current, Channel-Select or Enable Inputs	V <sub>in</sub> = V <sub>CC</sub> or GND, VEE = -6.0 V	6.0	± 0.1	± 1.0	± 1.0	μА
Icc	Maximum Quiescent Supply Current (per Package)	Channel Select, Enable and VIS = VCC or GND; VEE = GN VIO = 0 V VEE = -6		1 4	10 40	20 80	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## DC CHARACTERISTICS — Analog Section

					Guara	Guaranteed Limit		
Symbol	Parameter	Condition	Vcc	VEE	–55 to 25°C	≤85°C	≤125°C	Unit
R <sub>on</sub>	Maximum "ON" Resistance	$V_{in}$ = $V_{IL}$ or $V_{IH}$ ; $V_{IS}$ = $V_{CC}$ to $V_{EE}$ ; $I_S \le 2.0$ mA (Figures 1, 2)	4.5 4.5 6.0	0.0 - 4.5 - 6.0	190 120 100	240 150 125	280 170 140	Ω
		$V_{in} = V_{IL} \text{ or } V_{IH}; V_{IS} = V_{CC} \text{ or } V_{EE} \text{ (Endpoints)}; I_S \leq 2.0 \text{ mA} $ (Figures 1, 2)	4.5 4.5 6.0	0.0 -4.5 -6.0	150 100 80	190 125 100	230 140 115	
ΔR <sub>on</sub>	Maximum Difference in "ON" Resistance Between Any Two Channels in the Same Package	$\begin{split} &V_{in} = V_{IL} \text{ or } V_{IH}; \\ &V_{IS} = 1/2 \text{ (VCC} - V_{EE}); \\ &I_{S} \leq 2.0 \text{ mA} \end{split}$	4.5 4.5 6.0	0.0 - 4.5 - 6.0	30 12 10	35 15 12	40 18 14	Ω
l <sub>off</sub>	Maximum Off-Channel Leakage Current, Any One Channel	$V_{in} = V_{IL} \text{ or } V_{IH};$ $V_{IO} = V_{CC} - V_{EE};$ Switch Off (Figure 3)	6.0	-6.0	0.1	0.5	1.0	μА
	Maximum Off–Channel HC4051A Leakage Current, HC4052A Common Channel HC4053A		6.0 6.0 6.0	-6.0 -6.0 -6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	
l <sub>on</sub>	Maximum On–Channel HC4051A Leakage Current, HC4052A Channel–to–Channel HC4053A	Switch-to-Switch =	6.0 6.0 6.0	-6.0 -6.0 -6.0	0.2 0.1 0.1	2.0 1.0 1.0	4.0 2.0 2.0	μА

## **AC CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input $t_r = t_f = 6 \text{ ns}$ )

		VCC	Gu	aranteed Lim	nit	
Symbol	Parameter	V	–55 to 25°C	≤85°C	≤125°C	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Channel–Select to Analog Output (Figure 9)	2.0 3.0 4.5 6.0	270 90 59 45	320 110 79 65	350 125 85 75	ns
tPLH, tPHL	Maximum Propagation Delay, Analog Input to Analog Output (Figure 10)	2.0 3.0 4.5 6.0	40 25 12 10	60 30 15 13	70 32 18 15	ns
<sup>t</sup> PLZ <sup>,</sup> <sup>†</sup> PHZ	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 6.0	160 70 48 39	200 95 63 55	220 110 76 63	ns
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Propagation Delay, Enable to Analog Output (Figure 11)	2.0 3.0 4.5 6.0	245 115 49 39	315 145 69 58	345 155 83 67	ns
C <sub>in</sub>	Maximum Input Capacitance, Channel-Select or Enable Inputs		10	10	10	pF
C <sub>I/O</sub>	Maximum Capacitance Analog I/O		35	35	35	pF
	(All Switches Off)  Common O/I: HC4051A  HC4052A  HC4053A		130 80 50	130 80 50	130 80 50	
	Feedthrough		1.0	1.0	1.0	1

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D)

				Typical @ 25°C, V <sub>CC</sub> = 5.0 V, V <sub>EE</sub> = 0 V	
1	$C_PD$	Power Dissipation Capacitance (Figure 13)*	HC4051A	45	pF
1			HC4052A	80	
1			HC4053A	45	

<sup>\*</sup> Used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High–Speed CMOS Data Book (DL129/D).

## **ADDITIONAL APPLICATION CHARACTERISTICS (GND = 0 V)**

			VCC	VEE		Limit*		
Symbol	Parameter	Condition	V	v	25°C			Unit
BW	Maximum On–Channel Bandwidth or Minimum Frequency Response (Figure 6)	f <sub>in</sub> = 1MHz Sine Wave; Adjust f <sub>in</sub> Voltage to Obtain 0dBm at V <sub>OS</sub> ; Increase f <sub>in</sub> Frequency Until dB Meter Reads –3dB; R <sub>L</sub> = 50Ω, C <sub>L</sub> = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00	'51 80 80 80	'52 95 95 95	'53 120 120 120	MHz
_	Off-Channel Feedthrough Isolation (Figure 7)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at $V_{IS}$ $f_{in}$ = 10kHz, $R_L$ = 600 $\Omega$ , $C_L$ = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		$f_{in} = 1.0MHz, R_L = 50\Omega, C_L = 10pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00		-40 -40 -40		
_	Feedthrough Noise. Channel–Select Input to Common I/O (Figure 8)	$\begin{aligned} &V_{in} \leq \text{1MHz Square Wave } (t_r = t_f = 6\text{ns}); \\ &\text{Adjust R}_L \text{ at Setup so that I}_S = 0\text{A}; \\ &\text{Enable} = \text{GND} & \text{R}_L = 600\Omega, \text{C}_L = 50\text{pF} \end{aligned}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		25 105 135		mVpp
		R <sub>L</sub> = 10kΩ, C <sub>L</sub> = 10pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		35 145 190		
_	Crosstalk Between Any Two Switches (Figure 12) (Test does not apply to HC4051A)	$f_{in}$ = Sine Wave; Adjust $f_{in}$ Voltage to Obtain 0dBm at V <sub>IS</sub> $f_{in}$ = 10kHz, R <sub>L</sub> = 600 $\Omega$ , C <sub>L</sub> = 50pF	2.25 4.50 6.00	-2.25 -4.50 -6.00		-50 -50 -50		dB
		$f_{in} = 1.0MHz, R_L = 50\Omega, C_L = 10pF$	2.25 4.50 6.00	-2.25 -4.50 -6.00		-60 -60 -60		
THD	Total Harmonic Distortion (Figure 14)	$\begin{aligned} f_{In} &= 1 \text{kHz}, \ R_L = 10 \text{k}\Omega, \ C_L = 50 \text{pF} \\ \text{THD} &= \text{THD}_{measured} - \text{THD}_{source} \\ \text{V}_{IS} &= 4.0 \text{Vpp sine wave} \\ \text{V}_{IS} &= 8.0 \text{Vpp sine wave} \\ \text{V}_{IS} &= 11.0 \text{Vpp sine wave} \end{aligned}$	2.25 4.50 6.00	-2.25 -4.50 -6.00		0.10 0.08 0.05		%

<sup>\*</sup>Limits not tested. Determined by design and verified by qualification.

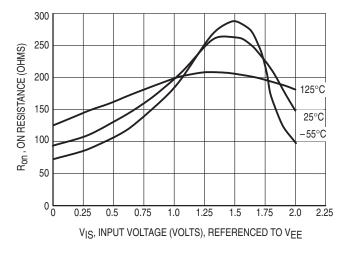


Figure 1a. Typical On Resistance,  $V_{CC} - V_{EE} = 2.0 \text{ V}$ 

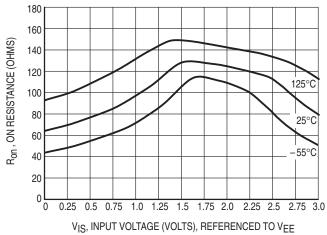
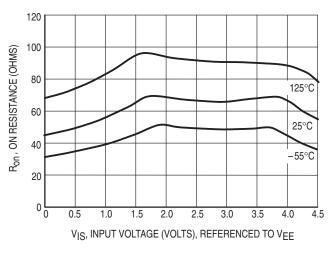


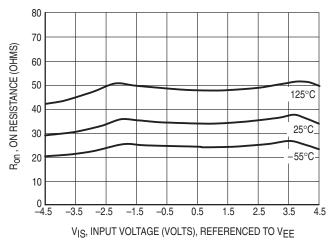
Figure 1b. Typical On Resistance,  $V_{CC} - V_{EE} = 3.0 \text{ V}$ 



105 90 75 60 45 30 0 0.5 1.0 1.5 2.0 2.5 3.0 3.5 4.0 4.5 5.0 5.5 6.0 VIS, INPUT VOLTAGE (VOLTS), REFERENCED TO VEE

Figure 1c. Typical On Resistance,  $V_{CC} - V_{EE} = 4.5 \text{ V}$ 

Figure 1d. Typical On Resistance, V<sub>CC</sub> - V<sub>EE</sub> = 6.0 V



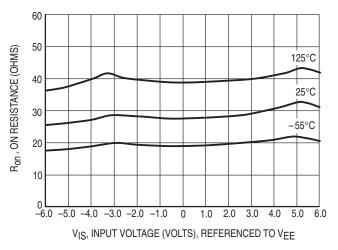


Figure 1e. Typical On Resistance,  $V_{CC} - V_{EE} = 9.0 \text{ V}$ 

Figure 1f. Typical On Resistance, V<sub>CC</sub> – V<sub>EE</sub> = 12.0 V

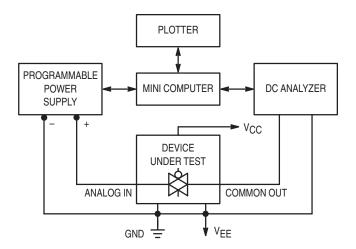


Figure 2. On Resistance Test Set-Up

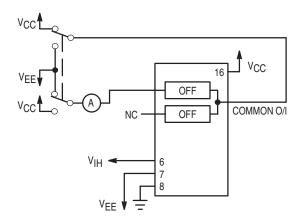


Figure 3. Maximum Off Channel Leakage Current, Any One Channel, Test Set-Up

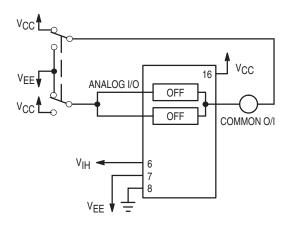


Figure 4. Maximum Off Channel Leakage Current, Common Channel, Test Set-Up

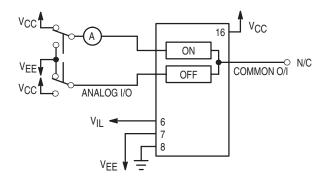


Figure 5. Maximum On Channel Leakage Current, Channel to Channel, Test Set-Up

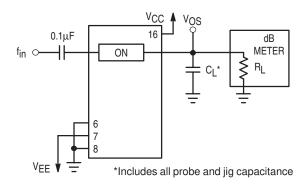


Figure 6. Maximum On Channel Bandwidth, Test Set-Up

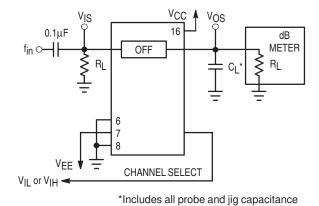
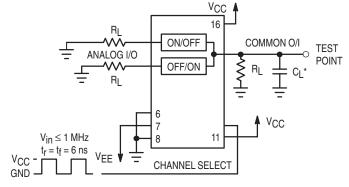


Figure 7. Off Channel Feedthrough Isolation, Test Set-Up



\*Includes all probe and jig capacitance

Figure 8. Feedthrough Noise, Channel Select to Common Out, Test Set-Up

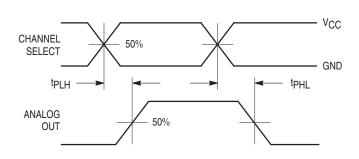
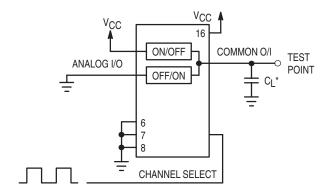


Figure 9a. Propagation Delays, Channel Select to Analog Out



\*Includes all probe and jig capacitance

VCC

Figure 9b. Propagation Delay, Test Set-Up Channel Select to Analog Out

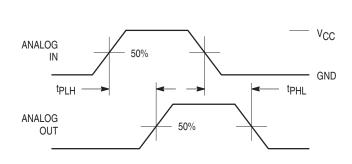


Figure 10a. Propagation Delays, Analog In to Analog Out

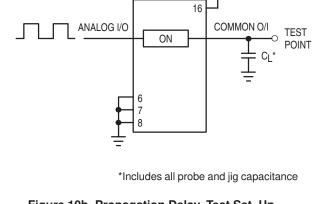


Figure 10b. Propagation Delay, Test Set-Up
Analog In to Analog Out

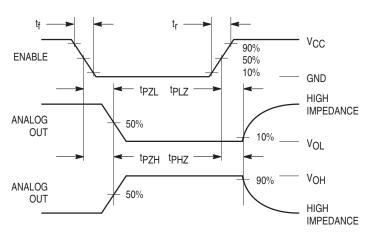


Figure 11a. Propagation Delays, Enable to Analog Out

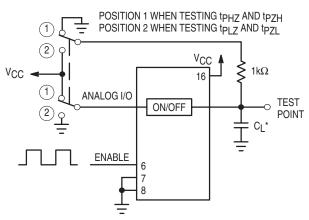
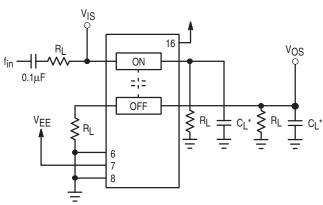


Figure 11b. Propagation Delay, Test Set-Up Enable to Analog Out



\*Includes all probe and jig capacitance

Figure 12. Crosstalk Between Any Two Switches, Test Set-Up

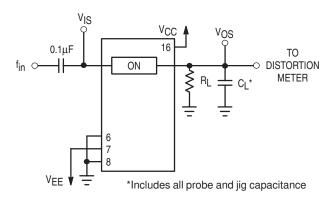


Figure 14a. Total Harmonic Distortion, Test Set-Up

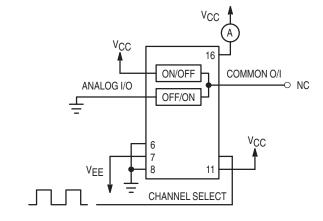


Figure 13. Power Dissipation Capacitance, Test Set-Up

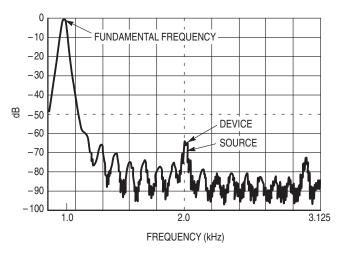


Figure 14b. Plot, Harmonic Distortion

#### **APPLICATIONS INFORMATION**

The Channel Select and Enable control pins should be at V<sub>CC</sub> or GND logic levels. V<sub>CC</sub> being recognized as a logic high and GND being recognized as a logic low. In this example:

$$V_{CC} = +5V = logic high$$
  
 $GND = 0V = logic low$ 

The maximum analog voltage swings are determined by the supply voltages  $V_{CC}$  and  $V_{EE}$ . The positive peak analog voltage should not exceed  $V_{CC}$ . Similarly, the negative peak analog voltage should not go below  $V_{EE}$ . In this example, the difference between  $V_{CC}$  and  $V_{EE}$  is ten volts. Therefore, using the configuration of Figure 15, a maximum analog signal of ten volts peak—to—peak can be controlled. Unused analog inputs/outputs may be left floating (i.e., not connected). However, tying unused analog inputs and

outputs to V<sub>CC</sub> or GND through a low value resistor helps minimize crosstalk and feedthrough noise that may be picked up by an unused switch.

Although used here, balanced supplies are not a requirement. The only constraints on the power supplies are that:

$$\begin{split} V_{CC}-GND &= 2 \text{ to 6 volts} \\ V_{EE}-GND &= 0 \text{ to -6 volts} \\ V_{CC}-V_{EE} &= 2 \text{ to } 12 \text{ volts} \\ \text{and } V_{EE} &\leq GND \end{split}$$

When voltage transients above  $V_{CC}$  and/or below  $V_{EE}$  are anticipated on the analog channels, external Germanium or Schottky diodes  $(D_X)$  are recommended as shown in Figure 16. These diodes should be able to absorb the maximum anticipated current surges during clipping.

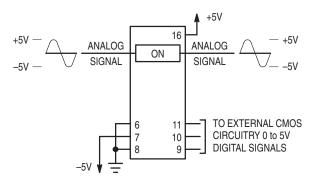


Figure 15. Application Example

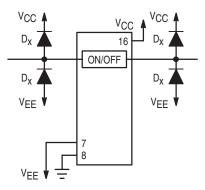
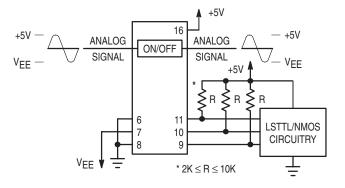
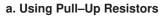
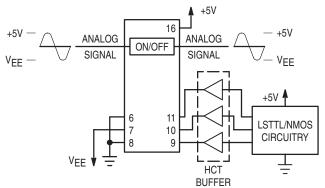


Figure 16. External Germanium or Schottky Clipping Diodes

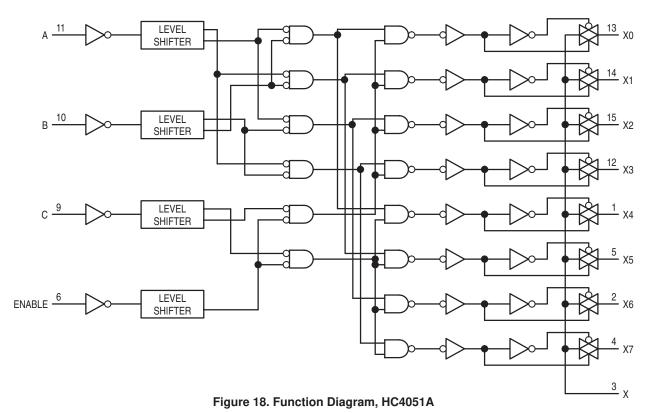






b. Using HCT Interface

Figure 17. Interfacing LSTTL/NMOS to CMOS Inputs



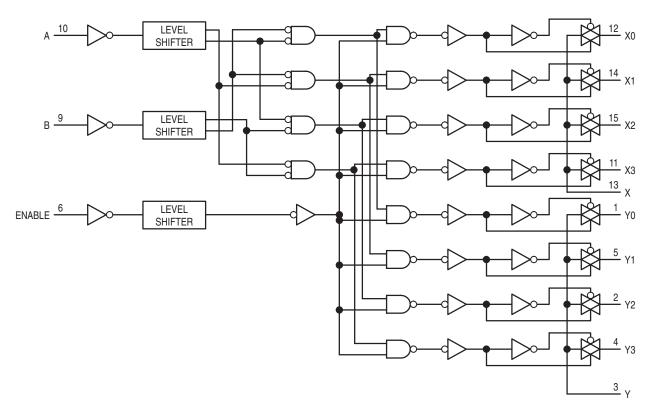


Figure 19. Function Diagram, HC4052A

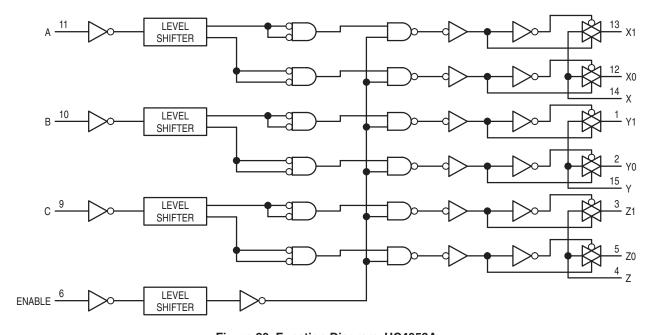


Figure 20. Function Diagram, HC4053A

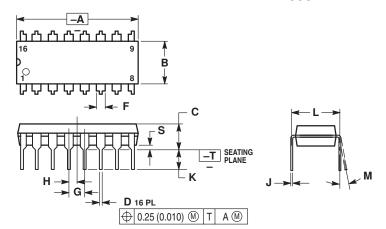
## **ORDERING & SHIPPING INFORMATION**

Device	Package	Shipping
MC74HC4051AN	PDIP-16	500 Units / Unit Pak
MC74HC4051AD	SOIC-16	48 Units / Rail
MC74HC4051ADR2	SOIC-16	2500 Units / Tape & Reel
MC74HC4051ADT	TSSOP-16	96 Units / Rail
MC74HC4051ADTR2	TSSOP-16	2500 Units / Tape & Reel
MC74HC4051ADW	SOIC WIDE	48 Units / Rail
MC74HC4051ADWR2	SOIC WIDE	1000 Units / Tape & Reel
MC74HC4051AF	SOEIAJ-16	See Note 1.
MC74HC4051AFEL	SOEIAJ-16	See Note 1.
MC74HC4052AN	PDIP-16	500 Units / Unit Pak
MC74HC4052AD	SOIC-16	48 Units / Rail
MC74HC4052ADR2	SOIC-16	2500 Units / Tape & Reel
MC74HC4052ADT	TSSOP-16	96 Units / Rail
MC74HC4052ADTR2	TSSOP-16	2500 Units / Tape & Reel
MC74HC4052ADW	SOIC WIDE	48 Units / Rail
MC74HC4052ADWR2	SOIC WIDE	1000 Units / Tape & Reel
MC74HC4052AF	SOEIAJ-16	See Note 1.
MC74HC4052AFEL	SOEIAJ-16	See Note 1.
MC74HC4053AN	PDIP-16	500 Units / Unit Pak
MC74HC4053AD	SOIC-16	48 Units / Rail
MC74HC4053ADR2	SOIC-16	2500 Units / Tape & Reel
MC74HC4053ADT	TSSOP-16	96 Units / Rail
MC74HC4053ADTR2	TSSOP-16	2500 Units / Tape & Reel
MC74HC4053ADW	SOIC WIDE	48 Units / Rail
MC74HC4053ADWR2	SOIC WIDE	1000 Units / Tape & Reel
MC74HC4053AF	SOEIAJ-16	See Note 1.
MC74HC4053AFEL	SOEIAJ-16	See Note 1.
	-	

<sup>1.</sup> For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

## **PACKAGE DIMENSIONS**

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE R

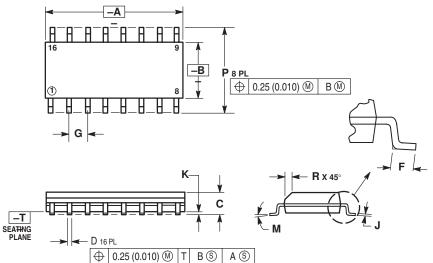


#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 174-3M, 1992.
   CONTROLLING DIMENSION: INCH.
   DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
   ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01





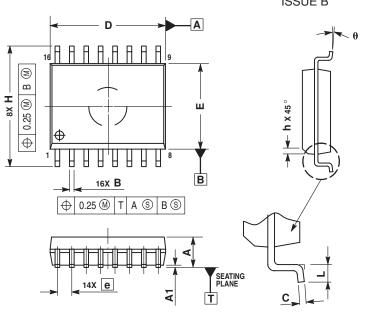
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI
- 7/14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
  DIMENSIONS A AND B DO NOT INCLUDE
  MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 (0.006)
  EDE SIDE. 3.
- PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR
  PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

## **PACKAGE DIMENSIONS**

### SOIC-16 WIDE **DW SUFFIX** CASE 751G-03 **ISSUE B**

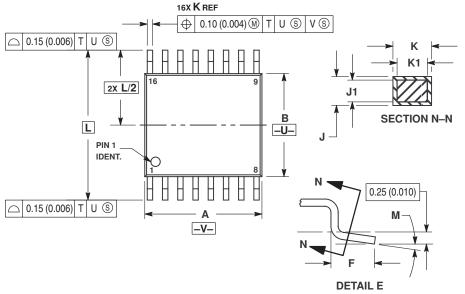


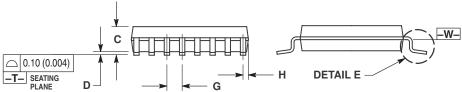
#### NOTES:

- DIMENSIONS ARE IN MILLIMETERS.
   INTERPRET DIMENSIONS AND TOLERANCES.
- PER ASME Y14.5M, 1994. DIMENSIONS D AND E DO NOT INLCUDE MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.
- DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF THE B DIMENSION AT MAXIMUM MATERIAL

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.35	2.65	
A1	0.10	0.25	
В	0.35	0.49	
С	0.23	0.32	
D	10.15	10.45	
Е	7.40	7.60	
е	1.27 BSC		
Н	10.05	10.55	
h	0.25	0.75	
L	0.50	0.90	
θ	0 °	7 °	

### TSSOP-16 **DT SUFFIX** CASE 948F-01 **ISSUE O**





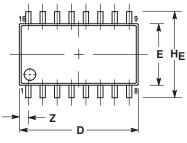
- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH.
  PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR
- PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-

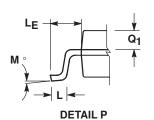
	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.18	0.28	0.007	0.011
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

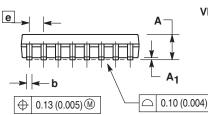
#### PACKAGE DIMENSIONS

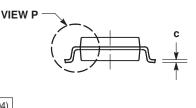
#### SOEIAJ-16 **F SUFFIX**

PLASTIC EIAJ SOIC PACKAGE CASE 966-01 **ISSUE O** 









#### NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
  Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.

  DIMENSIONS D AND E DO NOT INCLUDE
  MOLD FLASH OR PROTRUSIONS AND ARE
  MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PFR SIDE
- TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.

  THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018)

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
Α <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
ΗE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		0.78		0.031

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